



IXFH20N100P Information

www.helsssec.com

For Reference Only

Part Number IXFH20N100P

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1000V 20A TO-247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXFH20N100P Specifications

Manufacturer Part Number IXFH20N100P Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 660W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 660W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Manufacturer Part Number	IXFH20N100P
Package TO-247-3 Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 660W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Manufacturer	IXYS
Package TO-247-3 Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 660W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Category	Discrete Semiconductor Products
Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 660W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 660W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature 55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 70-247AD (IXFH) Package / Case	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature Supplier Device Package TO-247AD (IXFH) Package / Case MOSFET (Metal Oxide) 1000 1000 20A (Tc) 20A (Tc) 10V 20A (Tc) 20A (Tc) 20A (Tc) 20A (Tc) 20A (Tc) 6.5V @ ImA 6.5V @ ImA 6.5V @ 1mA 6.5V @ 1mA 6.5V @ 1mA 6.5V @ 1oV 7300pF @ 25V 7	Series	HiPerFET?, PolarP2?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-247AD (IXFH) Package / Case 20A (Tc) 21B (AC) 22B (AC) 22	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ### ### ### ### ### ### ### ### ### #	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature Supplier Device Package TO-247AD (IXFH) Package / Case	Drain to Source Voltage (Vdss)	1000V
Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 126nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 660W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	20A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-AD (IXFH) Package / Case	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 7300pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case	Vgs(th) (Max) @ Id	6.5V @ 1mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)660W (Tc)Rds On (Max) @ Id, Vgs570 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247AD (IXFH)Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	126nC @ 10V
FET Feature - G60W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	7300pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs570 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247AD (IXFH)Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Power Dissipation (Max)	660W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	570 mOhm @ 10A, 10V
Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247AD (IXFH)
Report errors?	Package / Case	TO-247-3
		Report errors?

IXFH20N100P Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFH20N100P Payment Methods



















IXFH20N100P Shipping Methods













If you have any question about IXFH20N100P, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com